

AS7C34098B

Revision History AS7C34098B

Revision	Details	Date
Rev 1.0	Initial Issue	Aug. 2016
Rev 2.0	Add TFBGA package	June. 2017

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AS7C34098B

256K X 16 BIT HIGH SPEED CMOS SRAM

FEATURES

■ Fast access time : 10ns ■ Low power consumption:

Operating current: 40mA (TYP.) Standby current: 2mA (TYP.)

■ Single 3.3V power supply

■ All inputs and outputs TTL compatible

■ Fully static operation

■ Tri-state output

■ Data byte control : LB# (DQ0 ~ DQ7) UB# (DQ8 ~ DQ15)

■ Data retention voltage : 1.5V (MIN.)

■ ROHS compliant

■ Package : 44-pin 400mil TSOP II

48-ball 6mm x 8mm TFBGA

GENERAL DESCRIPTION

The AS7C34098B is a 4,194,304-bit high speed CMOS static random access memory organized as 262,144 words by 16 bits. It is fabricated using very high performance, high reliability CMOS technology. Its standby current is stable within the range of operating temperature.

The AS7C34098B operates from a single power supply of 3.3V and all inputs and outputs are fully TTL compatible

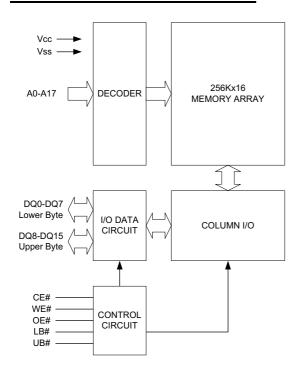
Table 1. Ordering Information

Part Number	Speed	Temperature	Vcc Range	Package
AS7C34098B-10TIN*	10ns	Industrial -40°C to +85°C	2.7 ~ 3.6V	44pin TSOPII
AS7C34098B-10BIN*	10ns	Industrial -40°C to +85°C	2.7 ~ 3.6V	48-ball TFBGA

^{*:} indicates Tray and add TR =Tape Reel packing type



FUNCTIONAL BLOCK DIAGRAM



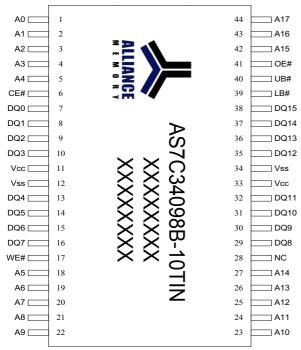
SYMBOL	DESCRIPTION
A0 - A17	Address Inputs
DQ0 - DQ15	Data Inputs/Outputs
CE#	Chip Enable Inputs
WE#	Write Enable Input
OE#	Output Enable Input
LB#	Lower Byte Control
UB#	Upper Byte Control
V _{CC}	Power Supply
V_{SS}	Ground
NC	No Connection

PIN DESCRIPTION

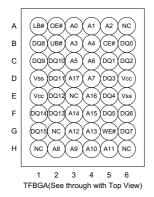
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PIN CONFIGURATION



TSOP II



TFBGA (Top View)

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ABSOLUTE MAXIMUM RATINGS*

PARAMETER	SYMBOL	RATING	UNIT
Voltage on V_{CC} relative to V_{SS}	V_{T1}	-0.5 to 4.6	V
Voltage on any other pin relative to V_{SS}	V_{T2}	-0.5 to V _{CC} +0.5	V
Operating Temperature	T _A	-40 to 85	$^{\circ}$
Storage Temperature	T _{STG}	-65 to 150	$^{\circ}$ C
Power Dissipation	P_{D}	1	W
DC Output Current	I _{OUT}	50	mA

^{*}Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

TRUTH TABLE

MODE	CE#	OE#	WE#	LB#	UB#	I/O OPE	RATION	SUPPLY CURRENT
WIODE	CE#	UE#	VV⊏#	LD#	UD#	DQ0 - DQ7	DQ8 - DQ15	SUPPLI CURRENT
Standby	Н	Х	Х	Х	Х	High-Z	High-Z	I _{SB} ,I _{SB1}
Output Disable	L	Н	Н	Х	Х	High-Z	High-Z	I_{CC},I_{CC1}
Output Disable	L	Χ	Χ	Η	Н	High-Z	High-Z	100,1001
	L	L	Ι	L	Ι	D_OUT	High-Z	
Read	L	L	Н	Н	L	High-Z	D_OUT	I_{CC},I_{CC1}
	L	L	Н	L	L	D_OUT	D_OUT	
	L	Х	L	L	I	D_IN	High-Z	
Write	L	Х	L	Н	L	High-Z	D_IN	I_{CC},I_{CC1}
	L	Х	L	L	L	D_IN	D_IN	

Note: $H = V_{IH}$, $L = V_{IL}$, X = Don't care

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DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP. *4	MAX.	UNIT
Supply Voltage	V _{cc}		2.7	3.3	3.6	V
Input High Voltage	V _{IH} *1		2.2	-	V _{CC} +0.3	V
Input Low Voltage	V _{IL} *2		- 0.3	-	0.8	V
Input Leakage Current	ILI	$V_{CC} \ge V_{IN} \ge V_{SS}$	- 1	-	1	μA
Output Leakage Current	I _{LO}	$V_{CC} \geqq V_{OUT} \geqq V_{SS},$ Output Disabled	- 1	-	1	μΑ
Output High Voltage	V _{OH}	$I_{OH} = -4mA$	2.4	-	-	V
Output Low Voltage	V_{OL}	$I_{OL} = 8mA$	-	-	0.4	V
Average Operating	Icc	Cycle time = MIN. CE# = V_{IL} , $I_{I/O}$ = 0mA, Others at V_{IL} or V_{IH}	-	50	70	mA
Power supply Current	I _{CC1}	CE# \leq 0.2, Others at 0.2V or V _{CC} -0.2V I _{I/O} = 0mA; f=MAX.	-	40	55	mA
Standby Power	I_{SB}	CE# = V_{IH} , Others at V_{IL} or V_{IH}	-	-	30	mA
Supply Current	I _{SB1}	CE# \geq V _{CC} - 0.2V, Others at 0.2V or V _{CC} - 0.2V	-	2	10	mA

Notes:

- 1. $V_{IH}(max) = V_{CC} + 2.0V$ for pulse width less than 6ns.
- 2. $V_{IL}(min) = V_{SS} 2.0V$ for pulse width less than 6ns.
- 3. Over/Undershoot specifications are characterized on engineering evaluation stage, not for mass production test.
- 4. Typical values are included for reference only and are not guaranteed or tested. Typical valued are measured at V_{CC} = V_{CC} (TYP.) and T_A = 25°C

CAPACITANCE (T_A = 25°C, f = 1.0MHz)

PARAMETER	SYMBOL	MIN.	MAX.	UNIT
Input Capacitance	C _{IN}	-	8	pF
Input/Output Capacitance	C _{I/O}	-	10	pF

Note: These parameters are guaranteed by device characterization, but not production tested.

AC TEST CONDITIONS

Speed	10ns
Input Pulse Levels	0.2V to V _{CC} - 0.2V
Input Rise and Fall Times	3ns
Input and Output Timing Reference Levels	1.5V
Output Load	$C_L = 30pF + 1TTL$, $I_{OH}/I_{OL} = -4mA/8mA$

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AC ELECTRICAL CHARACTERISTICS

(1) READ CYCLE

<u> </u>				
PARAMETER	SYM.	AS7C34	UNIT	
PARAMETER	STIVI.	MIN.	MAX.	UNII
Read Cycle Time	t _{RC}	10	-	ns
Address Access Time	t_{AA}	-	10	ns
Chip Enable Access Time	t _{ACE}	-	10	ns
Output Enable Access Time	t _{OE}	-	4.5	ns
Chip Enable to Output in Low-Z	t_{CLZ}^*	2	-	ns
Output Enable to Output in Low-Z	t_{OLZ}^*	0	-	ns
Chip Disable to Output in High-Z	t _{CHZ} *	-	4	ns
Output Disable to Output in High-Z	t _{OHZ} *	-	4	ns
Output Hold from Address Change	t _{OH}	2	-	ns
LB#, UB# Access Time	t _{BA}	-	4.5	ns
LB#, UB# to High-Z Output	t _{BHZ} *	-	4	ns
LB#, UB# to Low-Z Output	t _{BLZ} *	0	-	ns

(2) WRITE CYCLE

DADAMETED	0)/14	AS7C34		
PARAMETER	SYM.	MIN.	MAX.	UNIT
Write Cycle Time	t_{WC}	10	-	ns
Address Valid to End of Write	t_{AW}	8	-	ns
Chip Enable to End of Write	t_{CW}	8	-	ns
Address Set-up Time	t _{AS}	0	-	ns
Write Pulse Width	t_{WP}	8	-	ns
Write Recovery Time	t _{WR}	0	-	ns
Data to Write Time Overlap	t_{DW}	6	-	ns
Data Hold from End of Write Time	t_{DH}	0	-	ns
Output Active from End of Write	tow*	2	-	ns
Write to Output in High-Z	t _{WHZ} *	-	4	ns
LB#, UB# Valid to End of Write	t_{BW}	8	-	ns

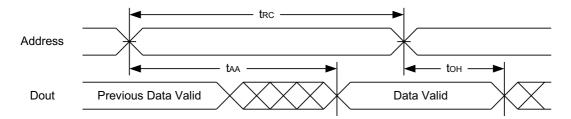
^{*}These parameters are guaranteed by device characterization, but not production tested.

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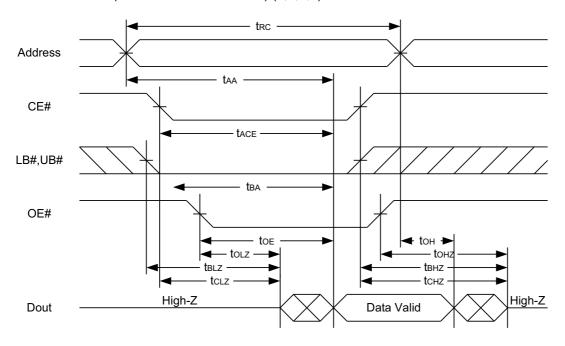


TIMING WAVEFORMS

READ CYCLE 1 (Address Controlled) (1,2)



READ CYCLE 2 (CE# and OE# Controlled) (1,3,4,5)



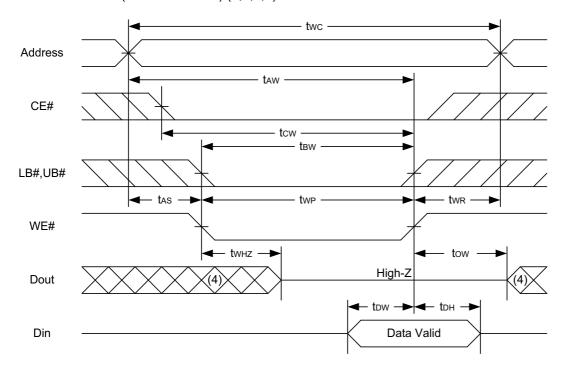
Notes:

- 1.WE# is high for read cycle.
- 2.Device is continuously selected OE# = low, CE# = low, LB# or UB# = low.
- 3.Address must be valid prior to or coincident with CE# = low, LB# or UB# = low transition; otherwise t_{AA} is the limiting parameter.
- $4.t_{CLZ}$, t_{BLZ} , t_{OLZ} , t_{CHZ} , t_{BHZ} and t_{OHZ} are specified with $C_L = 5pF$. Transition is measured $\pm 500mV$ from steady state.
- $5. At any given temperature and voltage condition, t_{CHZ} is less than t_{CLZ} \ , t_{BHZ} is less than t_{BLZ}, t_{OHZ} is less than t_{OLZ} is less than t_{CLZ} \ , t_{CHZ} is less than t_{CLZ}$

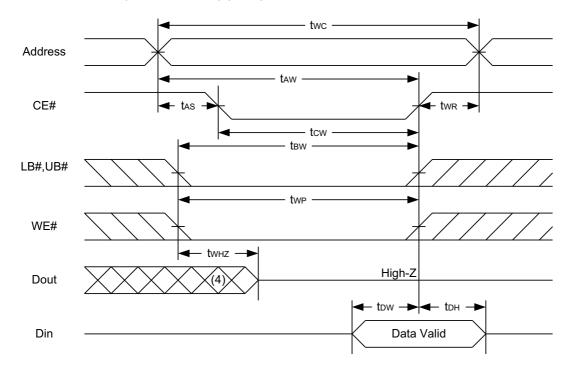
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WRITE CYCLE 1 (WE# Controlled) (1,2,4,5)

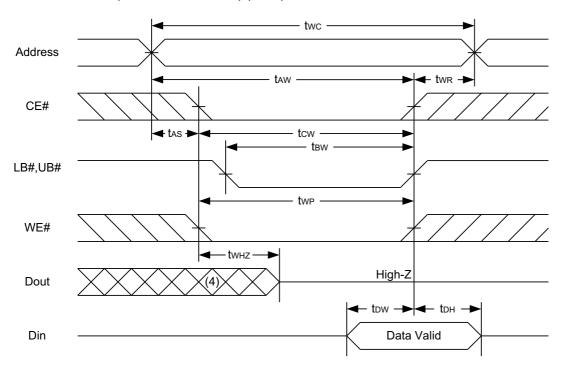


WRITE CYCLE 2 (CE# Controlled) (1,4,5)





WRITE CYCLE 3 (LB#,UB# Controlled) (1,4,5)



Notes:

- 1.A write occurs during the overlap of a low CE#, low WE#, LB# or UB# = low.
- 2.During a WE# controlled write cycle with OE# low, t_{WP} must be greater than t_{WHZ} + t_{DW} to allow the drivers to turn off and data to be placed on the bus.
- 3. During this period, I/O pins are in the output state, and input signals must not be applied.
- 4.If the CE#, LB#, UB# low transition occurs simultaneously with or after WE# low transition, the outputs remain in a high impedance state.
- $5.t_{\text{OW}}$ and t_{WHZ} are specified with C_L = 5pF. Transition is measured $\pm 500 \text{mV}$ from steady state.

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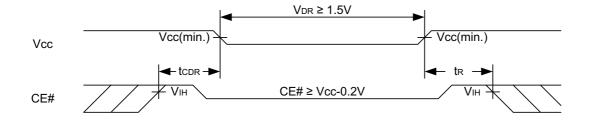


DATA RETENTION CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
V _{CC} for Data Retention	V_{DR}	$CE\# \ge V_{CC} - 0.2V$	1.5	-	3.6	V
Data Retention Current		V_{CC} = 1.5V, CE# \geq V_{CC} - 0.2V Others at 0.2V or V_{CC} - 0.2V	-	2	10	mA
Chip Disable to Data Retention Time	t _{CDR}	See Data Retention Waveforms (below)	0	-	-	ns
Recovery Time	t _R		t _{RC*}	-	-	ns

 t_{RC^*} = Read Cycle Time

DATA RETENTION WAVEFORM

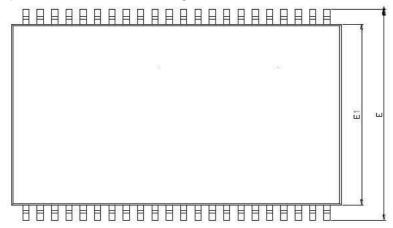


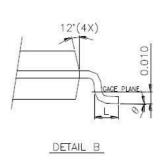
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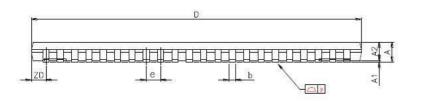


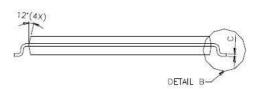
PACKAGE OUTLINE DIMENSION

44-pin 400 mil TSOP ${\rm I\hspace{-.1em}I}$ Package Outline Dimension









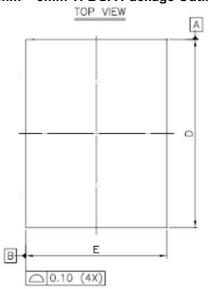
SYMBOLS	DIMENSI	ONS IN MILL	METERS	DIM	ENSIONS IN I	MILS
STWIBULS	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
Α	-	-	1.20	-	-	47.2
A1	0.05	0.10	0.15	2.0	3.9	5.9
A2	0.95	1.00	1.05	37.4	39.4	41.3
b	0.30	-	0.45	11.8	-	17.7
С	0.12	-	0.21	4.7	-	8.3
D	18.212	18.415	18.618	717	725	733
E	11.506	11.760	12.014	453	463	473
E1	9.957	10.160	10.363	392	400	408
е	i	0.800	-	-	31.5	-
L	0.40	0.50	0.60	15.7	19.7	23.6
ZD	-	0.805	-	-	31.7	-
У	-	-	0.076	-	-	3
θ	0°	3°	6°	0°	3°	6°

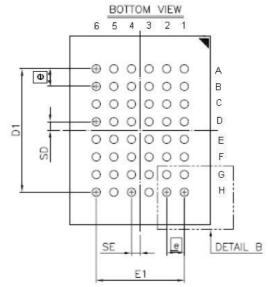
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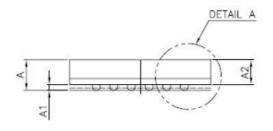




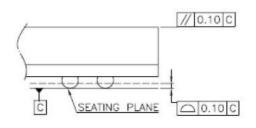
48-ball 6mm × 8mm TFBGA Package Outline Dimension



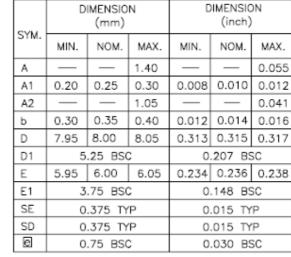


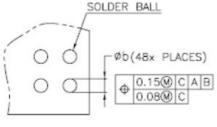


SIDE VIEW



DETAIL A





DETAIL B

NOTE:

- 1. CONTROLLING DIMENSION: MILLIMETER.
- 2. REFERENCE DOCUMENT : JEDEC MO-207.



AS7C34098B

ORDERING INFORMATION

Package Type	Access Time (Speed/ns)	Temperature Range(℃)	Packing Type	Alliance Memory Part Number
44-pin (400mil) TSOP II	10	-40°C ~85°C	Tray Tape Reel	AS7C34098B-10TIN AS7C34098B-10TINTR
48-ball			Tray	AS7C34098B-10BIN
(6mm x 8mm) TFBGA	10	-40℃~85℃	Tape Reel	AS7C34098B-10BINTR



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